Hydrogen interaction with impurities in silicon
Huy, P.T.

Citation for published version (APA):

General rights
It is not permitted to download or to forward/distribute the text or part of it without the consent of the author(s) and/or copyright holder(s), other than for strictly personal, individual use, unless the work is under an open content license (like Creative Commons).

Disclaimer/Complaints regulations
If you believe that digital publication of certain material infringes any of your rights or (privacy) interests, please let the Library know, stating your reasons. In case of a legitimate complaint, the Library will make the material inaccessible and/or remove it from the website. Please Ask the Library: http://uba.uva.nl/en/contact, or a letter to: Library of the University of Amsterdam, Secretariat, Singel 425, 1012 WP Amsterdam, The Netherlands. You will be contacted as soon as possible.
This thesis is based on the following publications:

1. Characterization of hydrogen and hydrogen-related centers in crystalline silicon by magnetic-resonance spectroscopy
   C. A. J. Ammerlaan and P. T. Huy

2. Hydrogen passivation of the selenium double donor in silicon: A study by magnetic resonance

3. Atomic and electronic structure of hydrogen-passivated double selenium donors in silicon
   P. T. Huy, C. A. J. Ammerlaan and T. Gregorkiewicz

   C. A. J. Ammerlaan and P. T. Huy

5. Magnetic-resonance investigation of gold and gold–hydrogen complexes in silicon
   P. T. Huy and C. A. J. Ammerlaan
   Submitted for publication in Phys. Rev. B (Chapter 4)

6. Complexes of gold and platinum with hydrogen in silicon
   P. T. Huy and C. A. J. Ammerlaan

7. EPR spectroscopy of Pt–H₃ and Pt–Fe₃ complexes in hydrogenated silicon
   P. T. Huy and C. A. J. Ammerlaan
   Submitted for publication in Phys. Rev. B (Chapter 5)

8. Hydrogen interaction with transition metals in silicon, studies by electron paramagnetic resonance
   P. T. Huy and C. A. J. Ammerlaan
   Solid State Phenom. 82–84, 133–138 (2001) (Chapters 5 and 6)

9. Electronic and atomic structure of transition metal–hydrogen complexes in silicon
   P. T. Huy and C. A. J. Ammerlaan
   Accepted for publication in Physica B 2001 (Chapters 5 and 6)
10. Silver-gold and gold-related centers observed in silver-doped p-type silicon by electron paramagnetic resonance.
   P. T. Huy and C. A. J. Ammerlaan
   In preparation for Phys. Rev. B (Chapter 7)

Other publications

   Trends in Materials Science and Technology (Hanoi National University Publishing House) (1999), pp. 52–55

12. Electron-paramagnetic-resonance studies of defects in electron-irradiated p-type 4H and 6H SiC

13. Influence of the doping distribution and the local electric field on the thermal emission of traps in the gamma irradiated mesa epitaxy silicon transistors
   P. N. Hai, D. T. Don and P. T. Huy

14. Gamma-irradiation-induced defects in silicon transistors, a study of DLTS
   P. T. Huy and D. T. Don

15. The influence of gamma irradiation on solar cell parameters
   T. D. Khoa, P. T. Huy and D. T. Don

16. The influence of structure of PN junction on the observation of middle band-gap deep levels in gamma irradiated silicon
   P. T. Huy and D. T. Don
“Nature uses only the longest threads to weave her patterns, so that each small piece of her fabric reveals the organization of the entire tapestry.”

- Richard Feynman -